

UNITED STATES PATENT AND TRADEMARK OFFICE

CERTIFICATE OF CORRECTION

PATENT NO. : 6,782,021 B2
 DATED : August 24, 2004
 INVENTOR(S) : Xiaodong Huang et al.

Page 1 of 5

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page.

Item [56], References Cited, U.S. PATENT DOCUMENTS, add:

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OTHER PUBLICATIONS, (cont.)

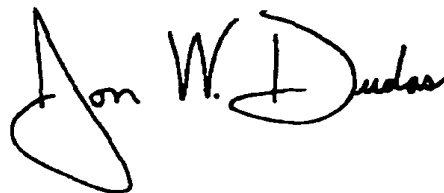
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Signed and Sealed this

Fourth Day of January, 2005



JON W. DUDAS
Director of the United States Patent and Trademark Office